

## P-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- Advanced trench cell design
- Low Thermal Resistance

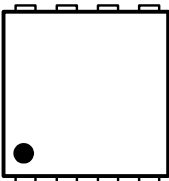
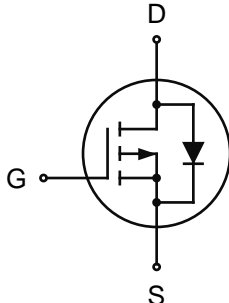
#### 1.2 Applications

- Motor drivers
- DC - DC Converter

#### 1.3 Quick reference

- $BV \geq -20\text{ V}$
- $P_{tot} \leq 20\text{ W}$
- $I_D \leq -50\text{ A}$
- $R_{DS(ON)} \leq 7\text{ m}\Omega @ V_{GS} = -10\text{ V}$
- $R_{DS(ON)} \leq 8\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
- $R_{DS(ON)} \leq 11\text{ m}\Omega @ V_{GS} = -2.5\text{ V}$

### 2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 <p>Top View PDFN3.3x3.3-8L</p>	
4	Gate		
5,6,7,8	Drain		

### 3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	Drain-Source Voltage	T <sub>C</sub> = 25 °C	-20	-	V
V <sub>GS</sub>	Gate-Source Voltage	T <sub>C</sub> = 25 °C	-	± 12	V
I <sub>D</sub> *	Drain Current	T <sub>C</sub> = 25 °C, V <sub>GS</sub> = -4.5 V	-	-50	A
I <sub>DM</sub> *,**,***	Pulsed Source Current	T <sub>C</sub> = 25 °C, V <sub>GS</sub> = -4.5 V	-	-96	A
P <sub>tot</sub> *	Total Power Dissipation	T <sub>C</sub> = 25 °C	-	20	W
T <sub>stg</sub>	Storage Temperature		- 55	150	°C
T <sub>J</sub>	Junction Temperature		-	150	°C
I <sub>S</sub>	Diode Forward Current	T <sub>C</sub> = 25 °C	-	-50	A
R <sub>θJC</sub> *	Thermal Resistance- Junction to Ambient		-	6	°C / W

Notes :

- \* Surface Mounted on 1 in<sup>2</sup> pad area, t ≤ 10 sec
- \*\* Pulse width ≤ 300 μs, duty cycle ≤ 1 %
- \*\*\* Limited by bonding wire

### 4. Marking Information

Product Name	Marking
KJ09P02Q	<div style="display: inline-block; border: 1px solid black; padding: 2px;"> <b>09P02</b>  <b>YWWXXX</b> </div> <b>YWW:</b> <b>Date Code</b>

### 5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ09P02Q	PDFN3.3x3.3-8L			5000	

Note: KUAJIJEXIN defines " Green " as lead-free ( RoHS compliant ) and halogen free ( Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C )

**6. Electrical Characteristics** ( $T_C = 25\text{ }^\circ\text{C}$  Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = -250\text{ }\mu\text{A}$	-0.3	-	-1.2	V
$I_{DSS}$	Zero Gate Voltage Source Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$	-	-	-10	$\mu\text{A}$
		$T_J = 85\text{ }^\circ\text{C}$	-	-	-30	$\mu\text{A}$
$I_{GSS}$	Gate Leakage Current	$V_{GS} = \pm 12\text{ V}, V_{DS} = 0\text{ V}$	-	-	$\pm 100$	nA
$R_{DS(on)}^a$	Drain-Source On-State Resistance	$V_{GS} = -10\text{ V}, I_D = -13\text{ A}$	-	6	7	$\text{m}\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$	-	7	8	$\text{m}\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -6\text{ A}$	-	10	11	$\text{m}\Omega$
<b>Diode Characteristics</b>						
$V_{SD}^a$	Diode Forward Voltage	$I_{SD} = -2.6\text{ A}, V_{GS} = 0\text{ V}$	-	-	-1.2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = -10\text{ A}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}$	-	36	-	nS
$Q_{rr}$	Reverse Recovery Charge		-	20	-	nC
<b>Dynamic Characteristics<sup>b</sup></b>						
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = -10\text{ V}$ Frequency = 1 MHz	-	6200	-	pF
$C_{oss}$	Output Capacitance		-	700	-	
$C_{rss}$	Reverse Transfer Capacitance		-	380	-	
$t_d(on)$	Turn-on Delay Time	$V_{DS} = -10\text{ V}, V_{GEN} = -5\text{ V},$ $R_G = 3.3\text{ }\Omega,$ $I_D = -1\text{ A}$	-	27	-	nS
$t_r$	Turn-on Rise Time		-	21	-	
$t_d(off)$	Turn-off Delay Time		-	240	-	
$t_f$	Turn-off Fall Time		-	110	-	
<b>Gate Charge Characteristics<sup>b</sup></b>						
$Q_g$	Total Gate Charge	$V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V},$ $I_{DS} = -10\text{ A}$	-	60	-	nC
$Q_{gs}$	Gate-Source Charge		-	10	-	
$Q_{gd}$	Gate-Drain Charge		-	13.5	-	

Notes :

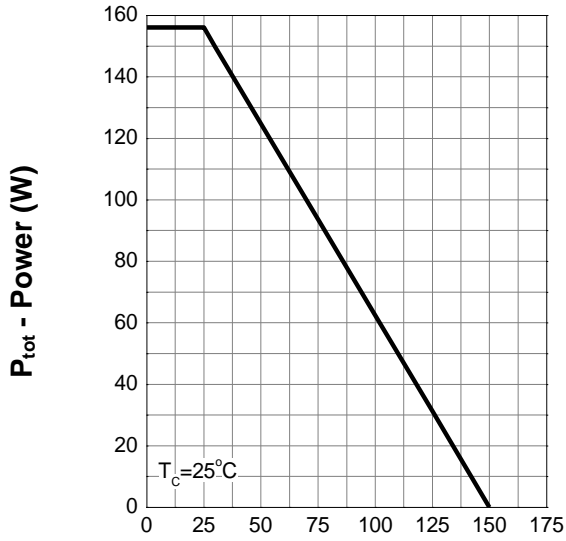
a : Pulse test ; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ 

b : Guaranteed by design, not subject to production testing



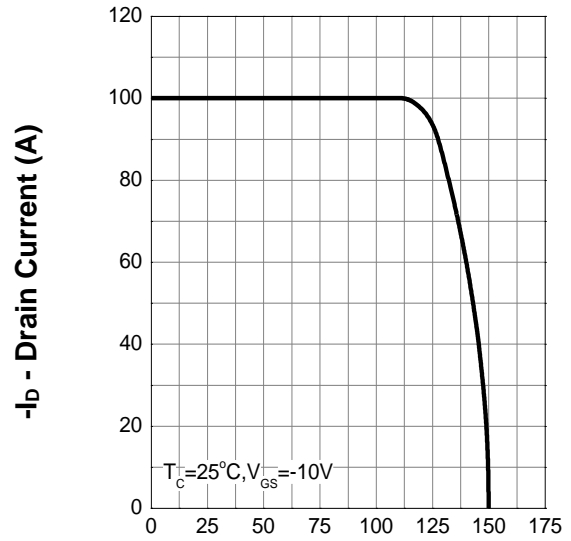
## 7. Typical Characteristics

### Power Capability



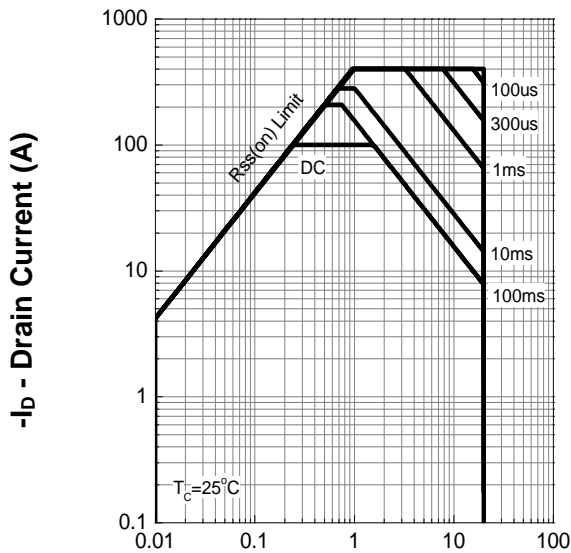
T<sub>j</sub> - Junction Temperature (°C)

### Current Capability



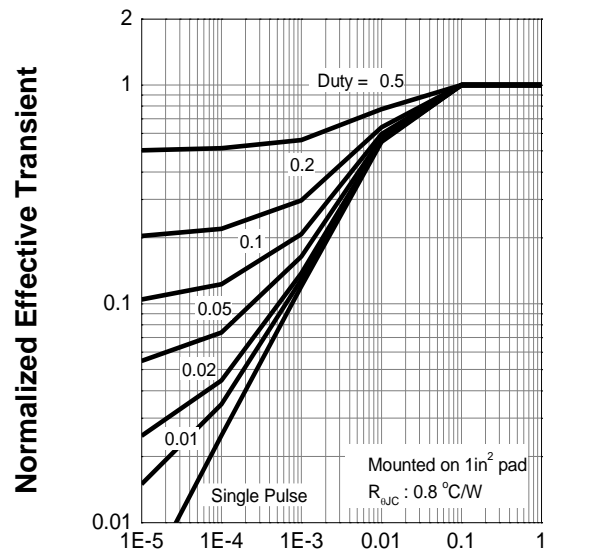
T<sub>j</sub> - Junction Temperature (°C)

### Safe Operation Area



-V<sub>DS</sub> - Drain-Source Voltage (V)

### Thermal Transient Impedance

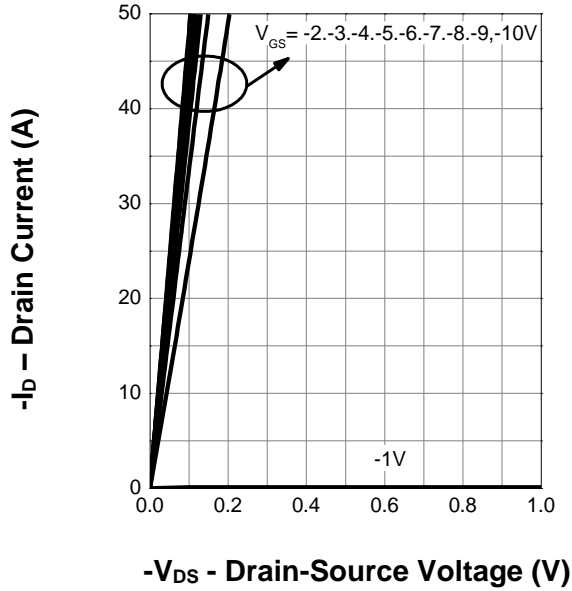


Square Wave Pulse Duration (sec)

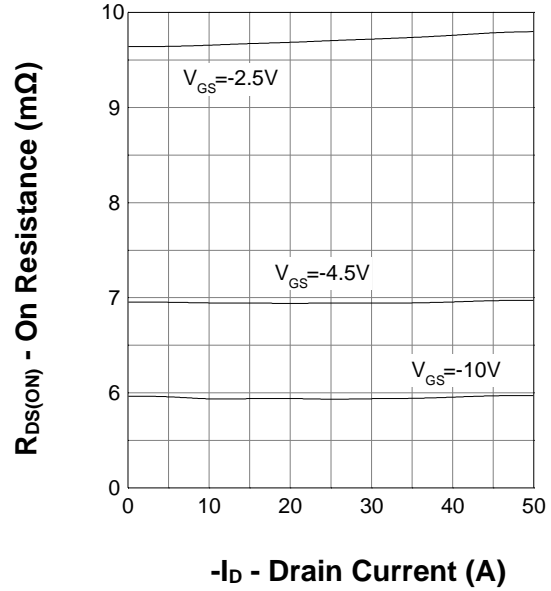


## 7. Typical Characteristics (cont.)

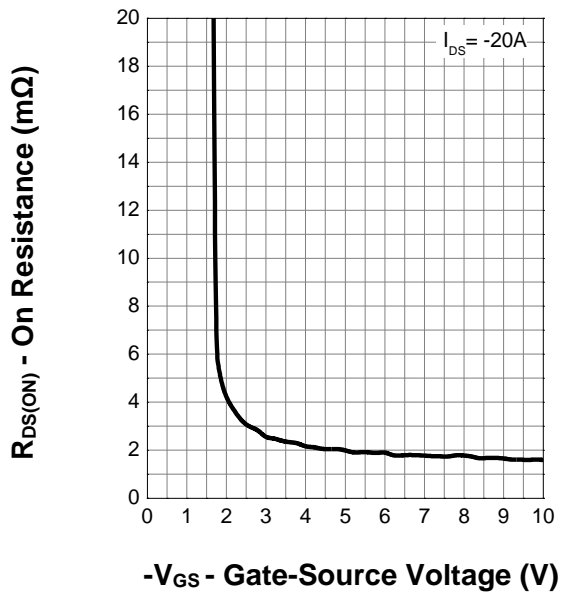
### Output Characteristics



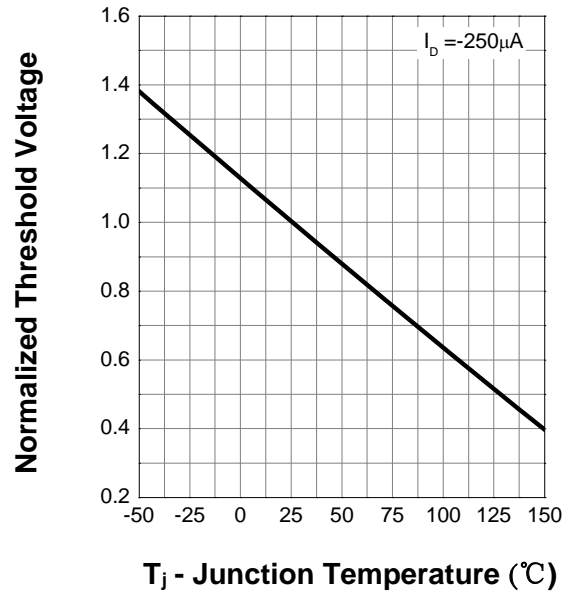
### Drain-Source On Resistance



### Transfer Characteristics



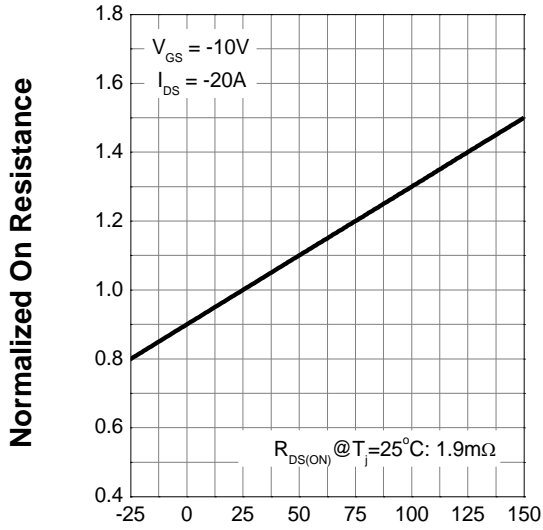
### Gate Threshold Voltage





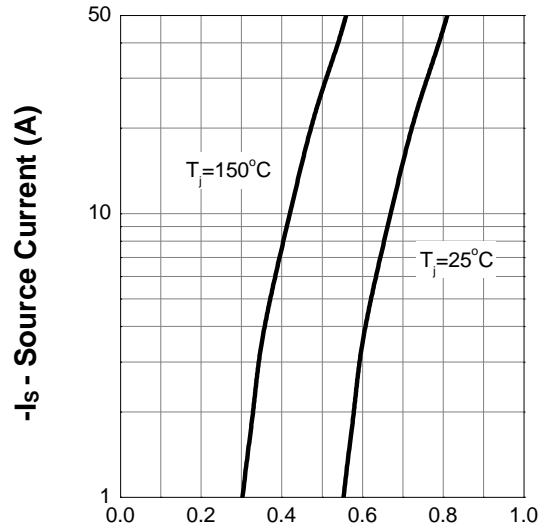
### 7. Typical Characteristics (cont.)

#### Drain-Source On Resistance



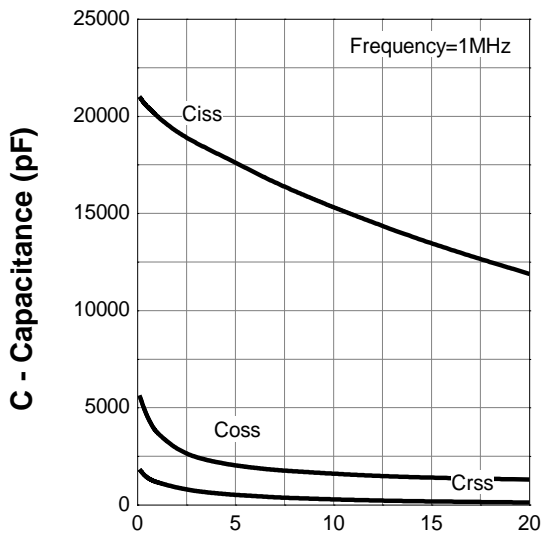
$T_j$  - Junction Temperature ( $^{\circ}\text{C}$ )

#### Body Diode Characteristics



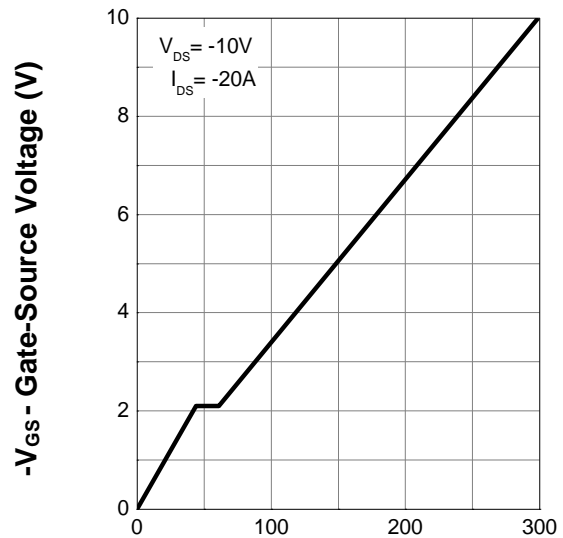
$-V_{SD}$  - Source-Drain Voltage (V)

#### Capacitance



$-V_{DS}$  - Drain-Source Voltage (V)

#### Gate Charge

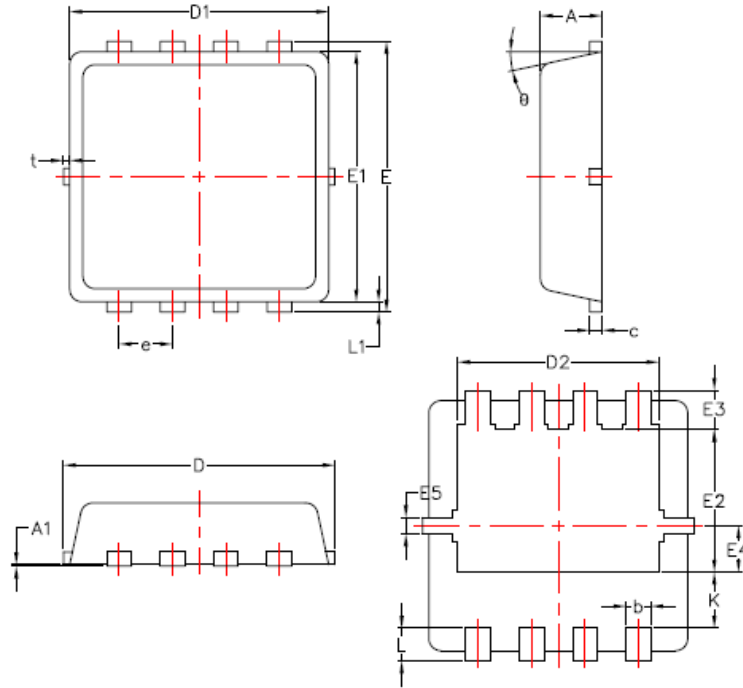


$Q_G$  - Gate Charge (nC)



### 8. Package Dimensions

PDFN3.3x3.3-8L Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	0.7	0.85
A1	/	0.05
b	0.20	0.40
c	0.10	0.25
D	3.15	3.45
D1	3.00	3.25
D2	2.29	2.65
E	3.15	3.45
E1	2.90	3.20
E2	1.54	1.94
E3	0.28	0.68
E4	0.37	0.77
E5	0.10	0.30
e	0.60	0.70
K	0.59	0.89
L	0.30	0.50
L1	0.06	0.20
T	0	0.13
θ	/	12°